

Product Summary

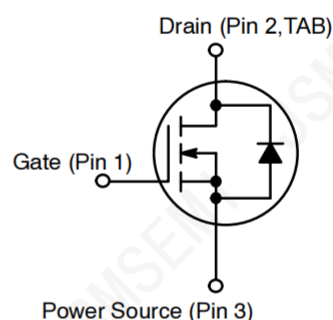
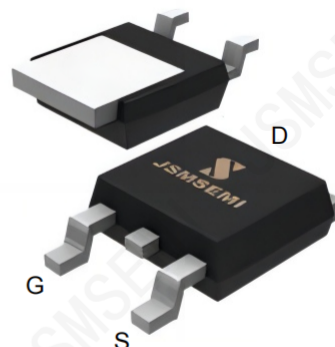
- V_{DS} 200V
- I_D 9A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<300m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Trench Power MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor
- Motor drivers



Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	200	V
Continuous Drain Current	I_D	9	A
Pulsed Drain Current (note1)	I_{DM}	36	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	115	mJ
Avalanche Current (note1)	I_{AS}	5	A
Repetitive Avalanche Energy (note1)	E_{AR}	69	mJ
Power Dissipation ($T_C = 25^\circ C$)	P_D	74	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	$-55 \sim +150$	$^\circ C$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.7	KW
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	

Specifications $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V, T_J = 25^{\circ}C$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, V_{DS} = 250\mu A$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4.5A$	--	0.25	0.3	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$	--	605	--	pF
Output Capacitance	C_{oss}		--	87	--	
Reverse Transfer Capacitance	C_{rss}		--	37	--	
Total Gate Charge	Q_g	$V_{DD} = 160V, I_D = 9A,$ $V_{GS} = 10V$	--	19	--	nC
Gate-Source Charge	Q_{gs}		--	3	--	
Gate-Drain Charge	Q_{gd}		--	8	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 100V, I_D = 9A,$ $R_G = 25\Omega$	--	35	--	ns
Turn-on Rise Time	t_r		--	7	--	
Turn-off Delay Time	$t_{d(off)}$		--	98	--	
Turn-off Fall Time	t_f		--	32	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^{\circ}C$	--	--	9	A
Pulsed Diode Forward Current	I_{SM}		--	--	36	
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}C, I_{SD} = 4.5A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 9A,$ $di_F/dt = 100A/\mu s$	--	145	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.82	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10mH, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Ordering Information

Order number	Package	Marking	Operation Temperature Range	MSL Grade	Ship, Quantity	Green
SUF630G-TN3-R	TO-252	JSM630D	-55 to 150°C	1	T&R, 2500	RoHS

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

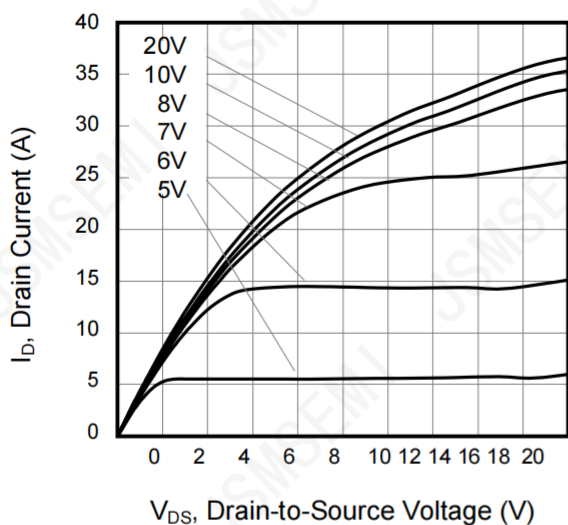
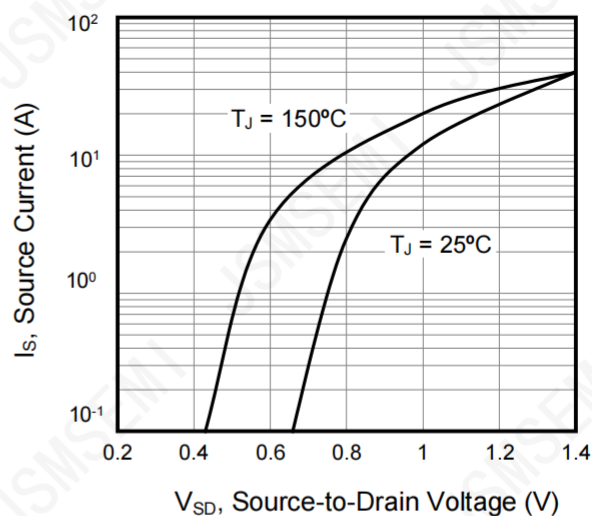
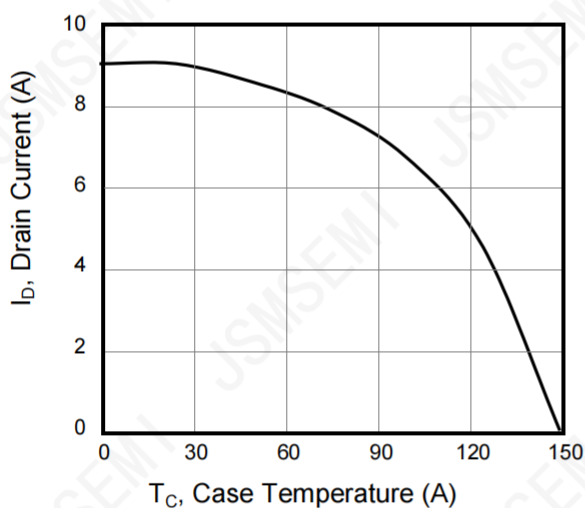
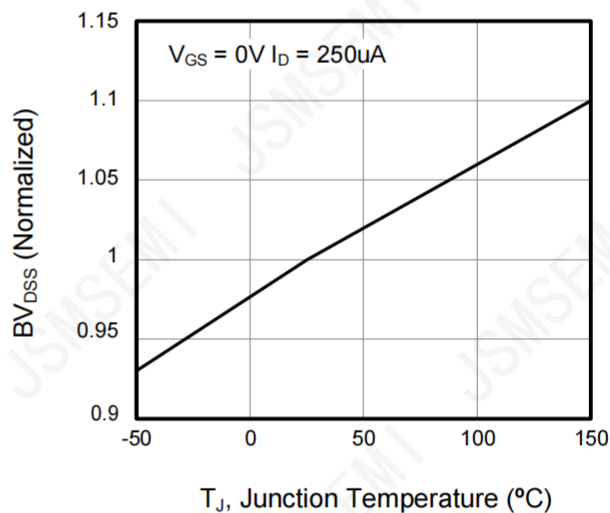
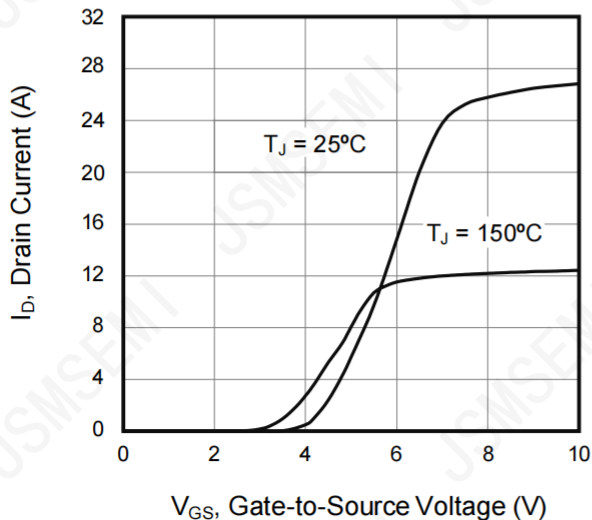
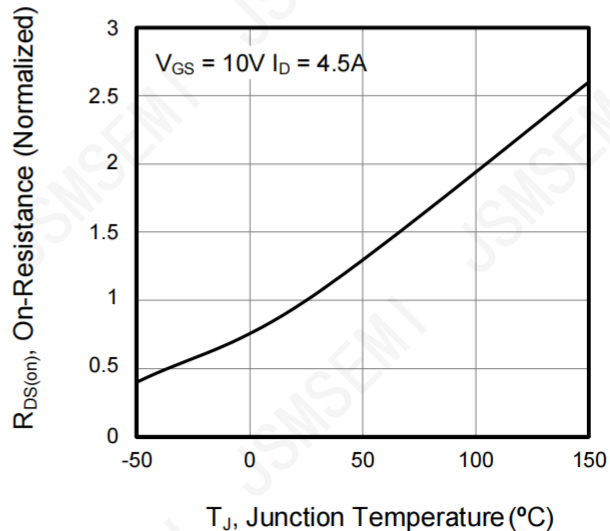
Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

Figure 2. Body Diode Forward Voltage

Figure 3. Drain Current vs. Temperature

Figure 4. BV_{DSS} Variation vs. Temperature

Figure 5. Transfer Characteristics

Figure 6. On-Resistance vs. Temperature


Figure 7. Capacitance

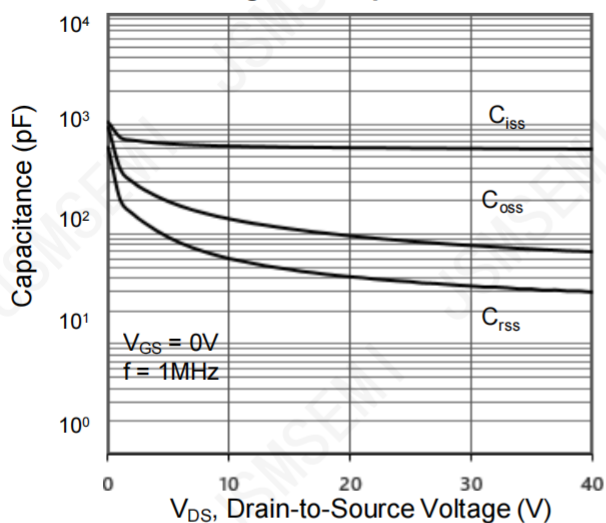


Figure 8. Gate Charge

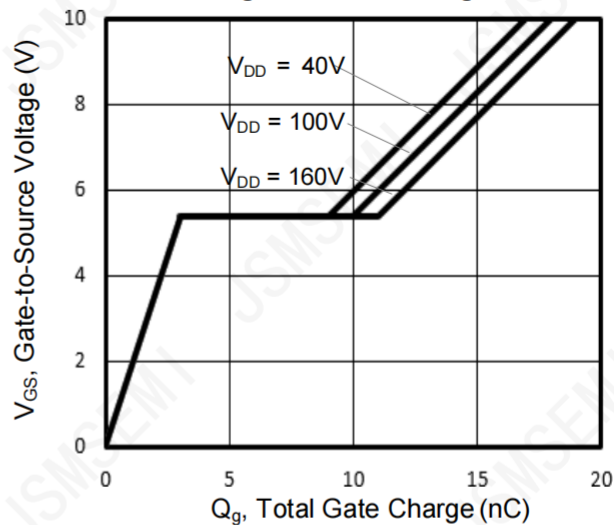


Figure 9. Transient Thermal Impedance

TO-252

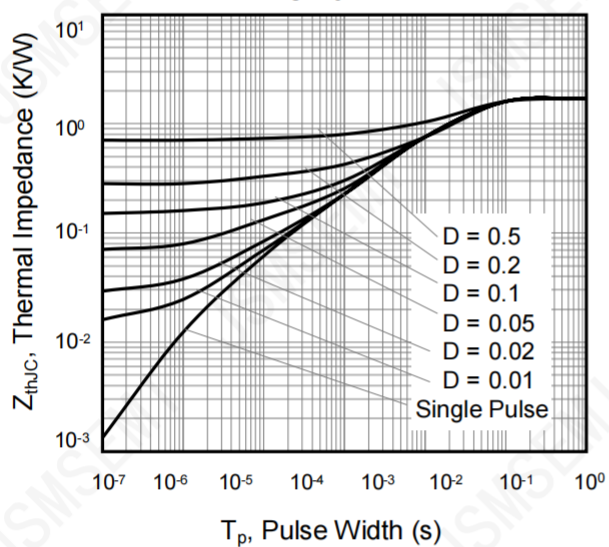


Figure A: Gate Charge Test Circuit and Waveform

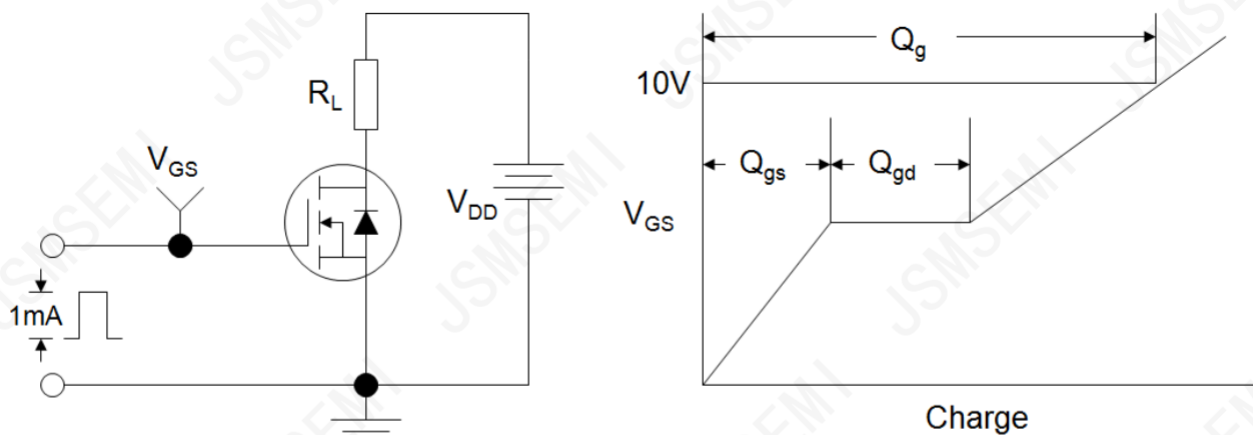


Figure B: Resistive Switching Test Circuit and Waveform

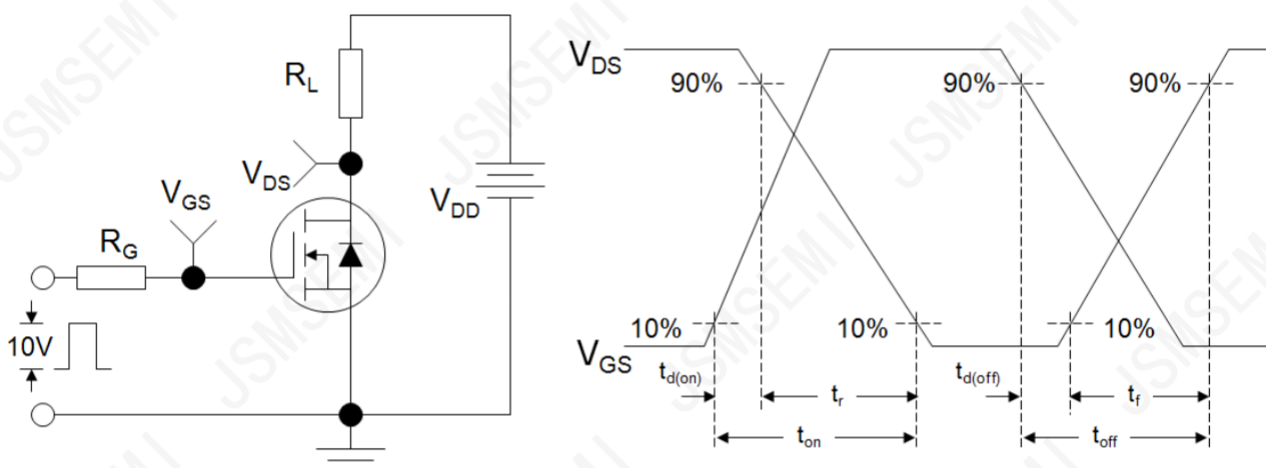
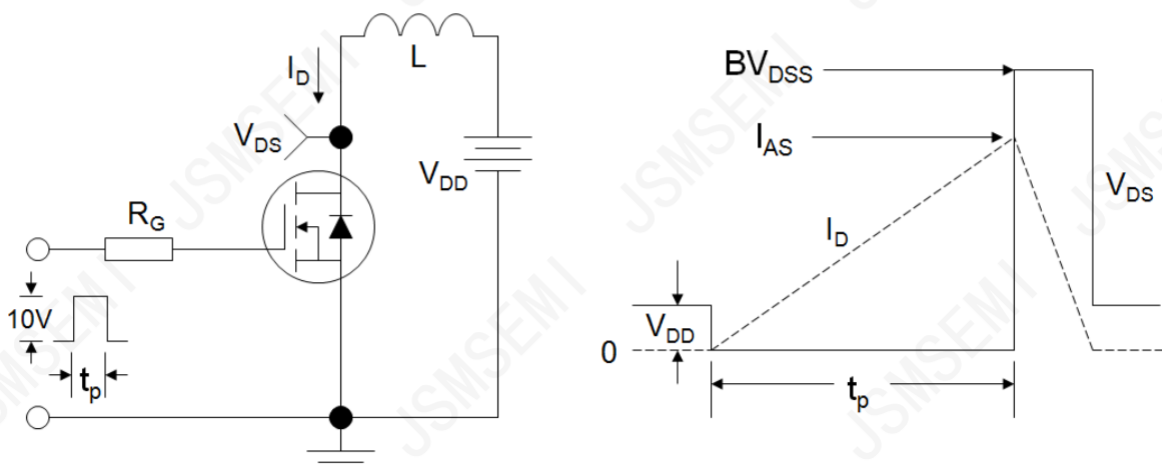
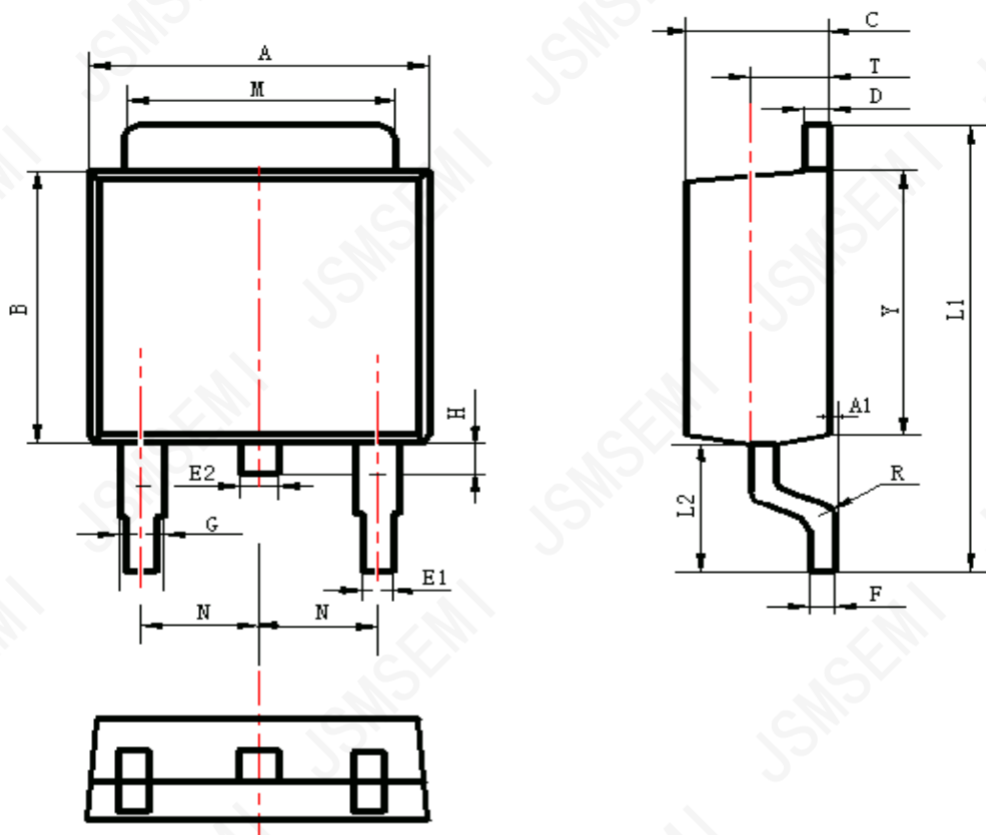


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	6.30	6.90	0.248	0.272
A1	0.00	0.16	0.000	0.006
B	5.70	6.30	0.224	0.248
C	2.10	2.50	0.083	0.098
D	0.30	0.70	0.012	0.028
E1	0.60	0.90	0.024	0.035
E2	0.70	1.00	0.028	0.039
F	0.30	0.60	0.012	0.024
G	0.70	1.20	0.028	0.047
L1	9.60	10.50	0.378	0.413
L2	2.70	3.10	0.106	0.122
H	0.40	1.00	0.016	0.039
M	5.10	5.50	0.201	0.217
N	2.09	2.49	0.082	0.098
R	0.30		0.012	
T	1.40	1.60	0.055	0.063
Y	5.10	6.30	0.201	0.248